Abstracts

Characterization of GaAs Devices by a Versatile Pulsed I-V Measurement System

A. Platzker, A. Palevsky, S. Nash, W. Struble and Y. Tajima. "Characterization of GaAs Devices by a Versatile Pulsed I-V Measurement System." 1990 MTT-S International Microwave Symposium Digest 90.3 (1990 Vol. III [MWSYM]): 1137-1140.

We have built and utilized a pulsed I-V system which is capable of reaching any current-voltage point of three-terminal devices from any arbitrarily chosen DC bias point. The system, which can be used on wafer, serves as an invaluable tool for device modeling and process diagnostics. Direct dependence of the pulsed I-V curves on the DC bias was found in GaAs MESFETs and HEMTs.

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